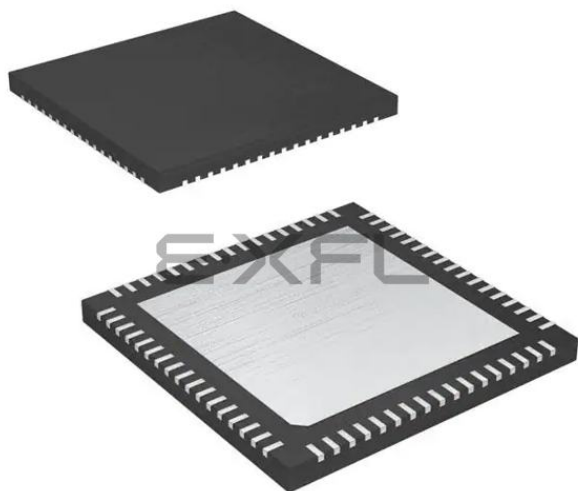




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl030v2-qng68i

Flash Advantages

Low Power

Flash-based IGLOO devices exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. IGLOO devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

IGLOO devices also have low dynamic power consumption to further maximize power savings; power is even further reduced by the use of a 1.2 V core voltage.

Low dynamic power consumption, combined with low static power consumption and Flash*Freeze technology, gives the IGLOO device the lowest total system power offered by any FPGA.

Security

Nonvolatile, flash-based IGLOO devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. IGLOO devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

IGLOO devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for intellectual property and configuration data. In addition, all FlashROM data in IGLOO devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. AES was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. IGLOO devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. IGLOO devices with AES-based security provide a high level of protection for remote field updates over public networks such as the Internet, and are designed to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the IGLOO family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The IGLOO family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. An IGLOO device provides the best available security for programmable logic designs.

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based IGLOO FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based IGLOO devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based IGLOO devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs. In addition, glitches and brownouts in system power will not corrupt the IGLOO device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based IGLOO devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

IGLOO flash FPGAs allow the user to quickly enter and exit Flash*Freeze mode. This is done almost instantly (within 1 μ s) and the device retains configuration and data in registers and RAM. Unlike SRAM-based FPGAs the device does not need to reload configuration and design state from external memory components; instead it retains all necessary information to resume operation immediately.

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, Flash-based IGLOO devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and

Table 2-36 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case
Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case V_{CCI} (per standard)
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVC MOS	8 mA	8	High	5	–	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
3.3 V LVC MOS Wide Range ³	100 μA	8	High	5	–	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
2.5 V LVC MOS	8 mA	8	High	5	–	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
1.8 V LVC MOS	4 mA	4	High	5	–	1.55	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	ns
1.5 V LVC MOS	2 mA	2	High	5	–	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns
1.2 V LVC MOS	1 mA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns
1.2 V LVC MOS Wide Range ³	100 μA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns

Notes:

1. The minimum drive strength for any LVC MOS 1.2 V or LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVC MOS 3.3 V software macros support LVC MOS 3.3 V wide range as specified in the JESD-8B specification.
3. All LVC MOS 1.2 V software macros support LVC MOS 1.2 V wide range as specified in the JESD8-12 specification
4. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Timing Characteristics*Applies to 1.5 V DC Core Voltage*

Table 2-51 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	4.47	0.18	0.85	0.66	4.56	3.89	2.24	2.19	8.15	7.48	ns
4 mA	Std.	0.97	4.47	0.18	0.85	0.66	4.56	3.89	2.24	2.19	8.15	7.48	ns
6 mA	Std.	0.97	3.74	0.18	0.85	0.66	3.82	3.37	2.49	2.63	7.42	6.96	ns
8 mA	Std.	0.97	3.74	0.18	0.85	0.66	3.82	3.37	2.49	2.63	7.42	6.96	ns
12 mA	Std.	0.97	3.23	0.18	0.85	0.66	3.30	2.98	2.66	2.91	6.89	6.57	ns
16 mA	Std.	0.97	3.08	0.18	0.85	0.66	3.14	2.89	2.70	2.99	6.74	6.48	ns
24 mA	Std.	0.97	3.00	0.18	0.85	0.66	3.06	2.91	2.74	3.27	6.66	6.50	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-52 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.73	0.18	0.85	0.66	2.79	2.22	2.25	2.32	6.38	5.82	ns
4 mA	Std.	0.97	2.73	0.18	0.85	0.66	2.79	2.22	2.25	2.32	6.38	5.82	ns
6 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.85	2.50	2.76	5.96	5.45	ns
8 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.85	2.50	2.76	5.96	5.45	ns
12 mA	Std.	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
16 mA	Std.	0.97	2.05	0.18	0.85	0.66	2.10	1.64	2.70	3.12	5.69	5.24	ns
24 mA	Std.	0.97	2.07	0.18	0.85	0.66	2.12	1.60	2.75	3.41	5.71	5.20	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-53 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.94	0.18	0.85	0.66	4.02	3.46	1.98	2.03	7.62	7.05	ns
4 mA	Std.	0.97	3.94	0.18	0.85	0.66	4.02	3.46	1.98	2.03	7.62	7.05	ns
6 mA	Std.	0.97	3.24	0.18	0.85	0.66	3.31	2.99	2.21	2.42	6.90	6.59	ns
8 mA	Std.	0.97	3.24	0.18	0.85	0.66	3.31	2.99	2.21	2.42	6.90	6.59	ns
12 mA	Std.	0.97	2.76	0.18	0.85	0.66	2.82	2.63	2.36	2.68	6.42	6.22	ns
16 mA	Std.	0.97	2.76	0.18	0.85	0.66	2.82	2.63	2.36	2.68	6.42	6.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-86 • 2.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.36	0.18	1.08	0.66	2.41	2.21	1.96	1.92	6.01	5.81	ns
4 mA	Std.	0.97	2.36	0.18	1.08	0.66	2.41	2.21	1.96	1.92	6.01	5.81	ns
6 mA	Std.	0.97	1.97	0.18	1.08	0.66	2.01	1.75	2.21	2.40	5.61	5.34	ns
8 mA	Std.	0.97	1.97	0.18	1.08	0.66	2.01	1.75	2.21	2.40	5.61	5.34	ns
12 mA	Std.	0.97	1.75	0.18	1.08	0.66	1.79	1.52	2.38	2.70	5.39	5.11	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-87 • 2.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	4.27	0.18	1.04	0.66	4.36	4.06	1.71	1.62	ns
4 mA	Std.	0.97	4.27	0.18	1.04	0.66	4.36	4.06	1.71	1.62	ns
6 mA	Std.	0.97	3.54	0.18	1.04	0.66	3.61	3.48	1.95	2.08	ns
8 mA	Std.	0.97	3.54	0.18	1.04	0.66	3.61	3.48	1.95	2.08	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-88 • 2.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.24	0.18	1.04	0.66	2.29	2.09	1.71	1.68	ns
4 mA	Std.	0.97	2.24	0.18	1.04	0.66	2.29	2.09	1.71	1.68	ns
6 mA	Std.	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
8 mA	Std.	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-92 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
4 mA	Std.	1.55	2.91	0.26	1.19	1.10	2.95	2.66	2.50	2.72	8.74	8.45	ns
6 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
8 mA	Std.	1.55	2.51	0.26	1.19	1.10	2.54	2.18	2.75	3.21	8.33	7.97	ns
12 mA	Std.	1.55	2.29	0.26	1.19	1.10	2.32	1.94	2.94	3.52	8.10	7.73	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-93 • 2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
4 mA	Std.	1.55	4.85	0.26	1.15	1.10	4.93	4.55	2.13	2.24	ns
6 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns
8 mA	Std.	1.55	4.09	0.26	1.15	1.10	4.16	3.95	2.38	2.71	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-94 • 2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
4 mA	Std.	1.55	2.76	0.26	1.15	1.10	2.80	2.52	2.13	2.32	ns
6 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
8 mA	Std.	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-100 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.01	0.66	3.21	3.25	2.33	1.61	6.80	6.85	ns
4 mA	Std.	0.97	2.62	0.18	1.01	0.66	2.68	2.51	2.66	2.46	6.27	6.11	ns
6 mA	Std.	0.97	2.31	0.18	1.01	0.66	2.36	2.15	2.90	2.87	5.95	5.75	ns
8 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.08	2.95	2.98	5.89	5.68	ns
12 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
16 mA	Std.	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-101 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	5.78	0.18	1.01	0.66	5.90	5.32	1.95	1.47	9.49	8.91	ns
4 mA	Std.	0.97	4.75	0.18	1.01	0.66	4.85	4.54	2.25	2.21	8.44	8.13	ns
6 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns
8 mA	Std.	0.97	4.07	0.18	1.01	0.66	4.15	3.98	2.46	2.58	7.75	7.57	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-102 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.76	0.18	1.01	0.66	2.79	2.76	1.94	1.51	6.39	6.35	ns
4 mA	Std.	0.97	2.25	0.18	1.01	0.66	2.30	2.09	2.24	2.29	5.89	5.69	ns
6 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
8 mA	Std.	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-103 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.63	0.18	0.98	0.66	5.74	5.30	1.68	1.24	ns
4 mA	Std.	0.97	4.69	0.18	0.98	0.66	4.79	4.52	1.97	1.98	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-107 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.32	0.26	1.11	1.10	6.43	5.81	2.47	2.16	12.22	11.60	ns
4 mA	Std.	1.55	5.27	0.26	1.11	1.10	5.35	5.01	2.78	2.92	11.14	10.79	ns
6 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns
8 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-108 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.11	1.10	3.26	3.18	2.47	2.20	9.05	8.97	ns
4 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.75	2.50	2.78	3.01	8.54	8.29	ns
6 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
8 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-109 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.13	0.26	1.08	1.10	6.24	5.79	2.08	1.78	ns
4 mA	Std.	1.55	5.17	0.26	1.08	1.10	5.26	4.98	2.38	2.54	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-110 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	3.06	0.26	1.08	1.10	3.10	3.01	2.08	1.83	3.06	ns
4 mA	Std.	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	2.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-135 • 1.2 V LVC MOS High SlewCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 1.14\text{ V}$

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	Std.	1.55	8.57	0.26	1.53	1.10	8.23	7.38	2.51	2.39	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-136 • 1.2 V LVC MOS High Slew – Applies to 1.2 V DC Core VoltageCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 1.14\text{ V}$

Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	Std.	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V LVC MOS Wide Range

Table 2-137 • Minimum and Maximum DC Input and Output Levels for LVC MOS 1.2 V Wide Range

Applicable to Advanced I/O Banks

1.2 V LVC MOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Equivalent Software Default Drive Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ⁴	Max. mA ⁴	μA^5	μA^5
100 μA	2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

- The minimum drive strength for the default LVC MOS 1.2 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.
- IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
- IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
- Currents are measured at 100°C junction temperature and maximum voltage.
- Currents are measured at 85°C junction temperature.
- Software default selection highlighted in gray.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

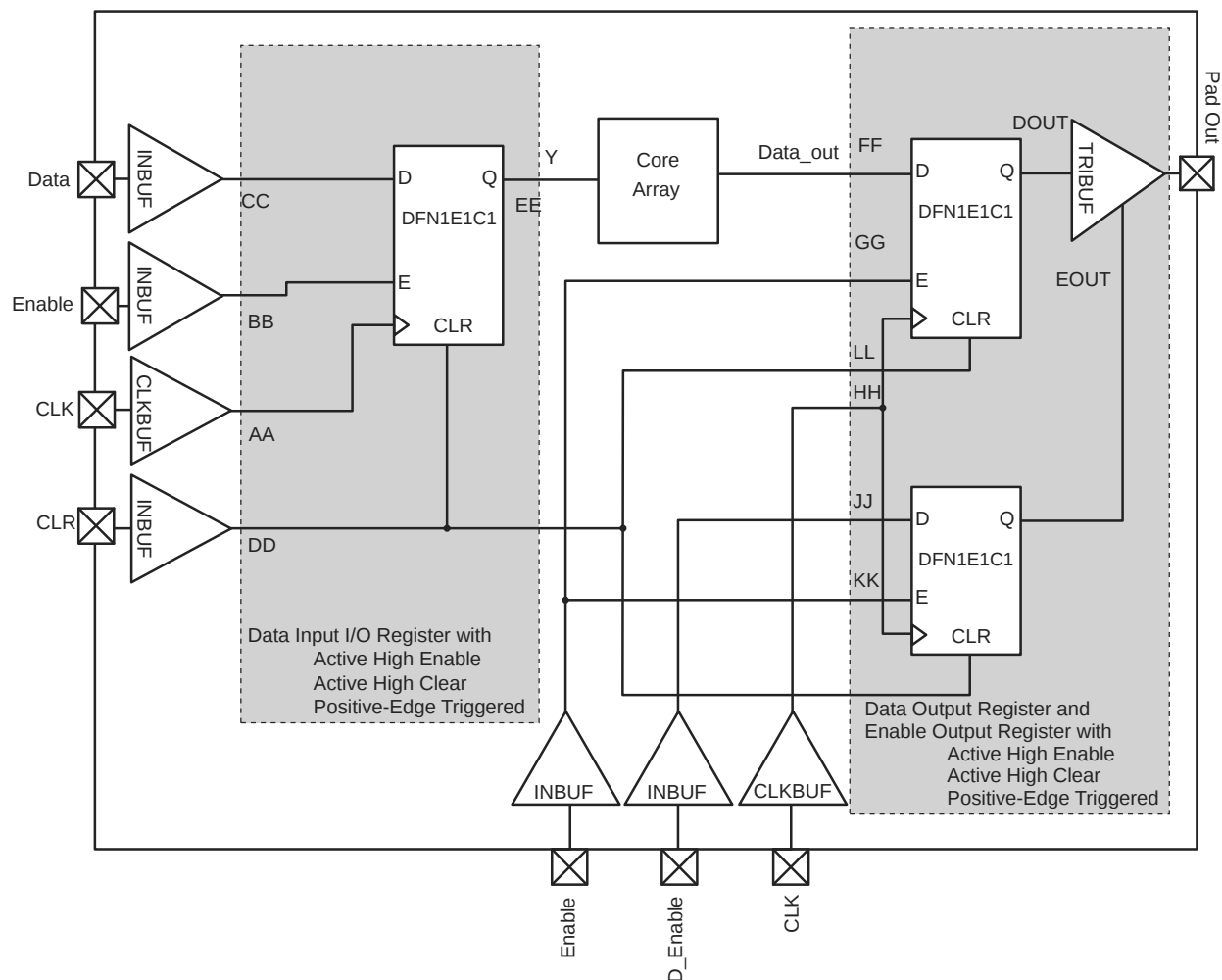


Figure 2-17 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

Input Register

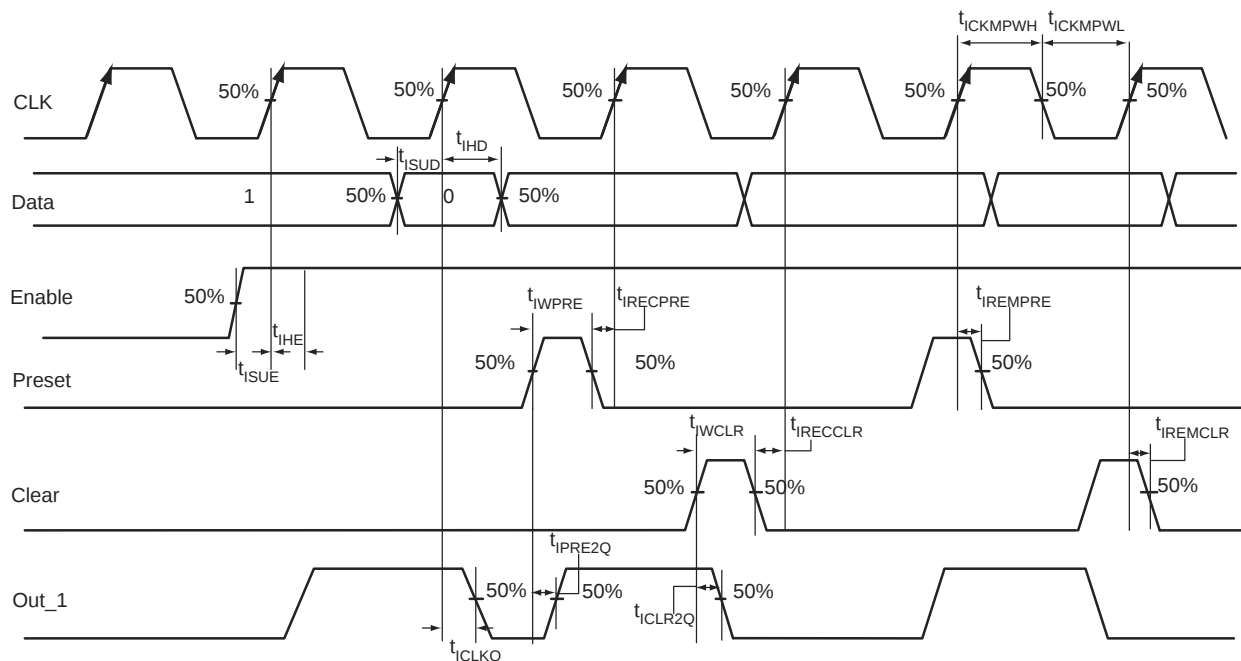


Figure 2-18 • Input Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-157 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.42	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.47	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.67	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
t_{IEMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t_{IREMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

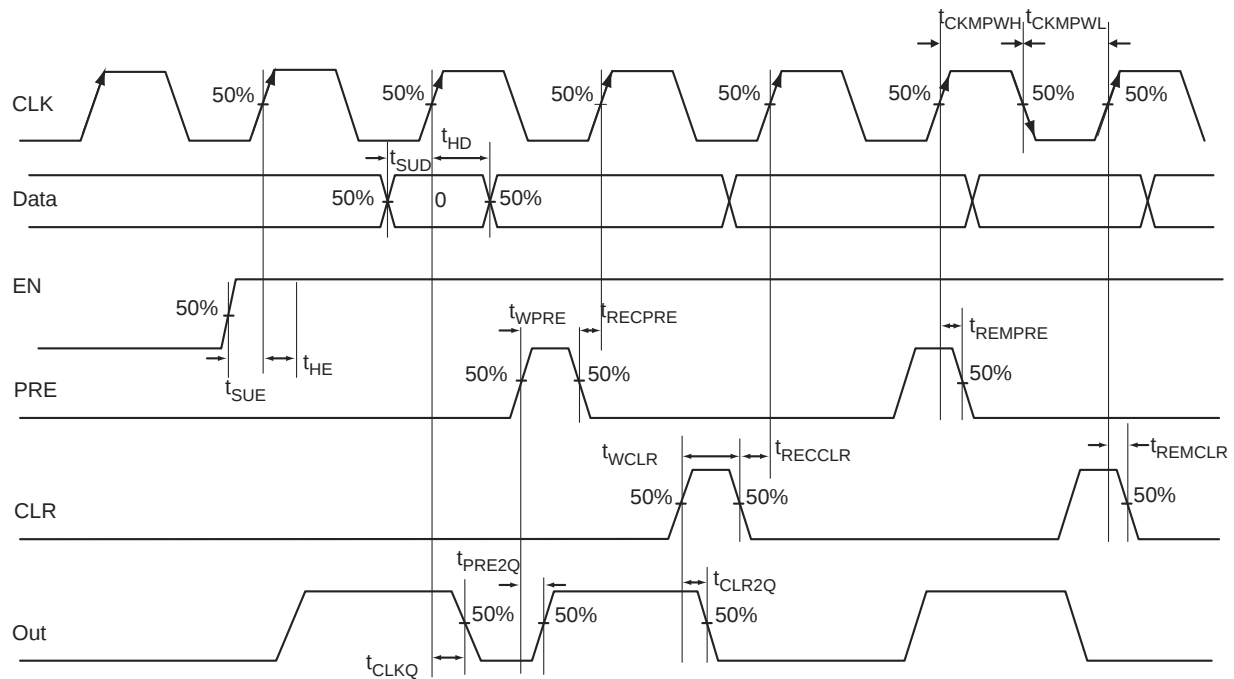


Figure 2-28 • Timing Model and Waveforms

Timing Characteristics

1.5 V DC Core Voltage

Table 2-171 • Register Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t_{SUD}	Data Setup Time for the Core Register	0.81	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.73	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.56	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-192 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.73	ns
t_{ENH}	REN, WEN hold time	0.08	ns
t_{DS}	Input data (WD) setup time	0.71	ns
t_{DH}	Input data (WD) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	4.21	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.71	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address - Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address - Applicable to Opening Edge	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	2.06	ns
	RESET Low to data out Low on RD (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

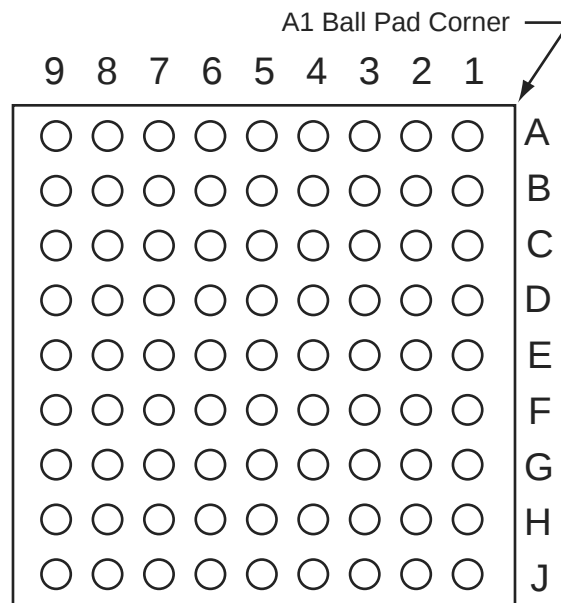
1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage**Table 2-196 • FIFO****Worst Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.13	ns
t_{ENH}	REN, WEN Hold Time	0.31	ns
t_{BKS}	BLK Setup Time	0.47	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	1.56	ns
t_{DH}	Input Data (WD) Hold Time	0.49	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	6.80	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	3.62	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	7.23	ns
t_{WCKFF}	WCLK High to Full Flag Valid	6.85	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	26.61	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	7.12	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	26.33	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	4.09	ns
	RESET Low to Data Out Low on RD (pipelined)	4.09	ns
t_{REMRSTB}	RESET Removal	1.23	ns
t_{RECRSTB}	RESET Recovery	6.58	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency for FIFO	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

CS81

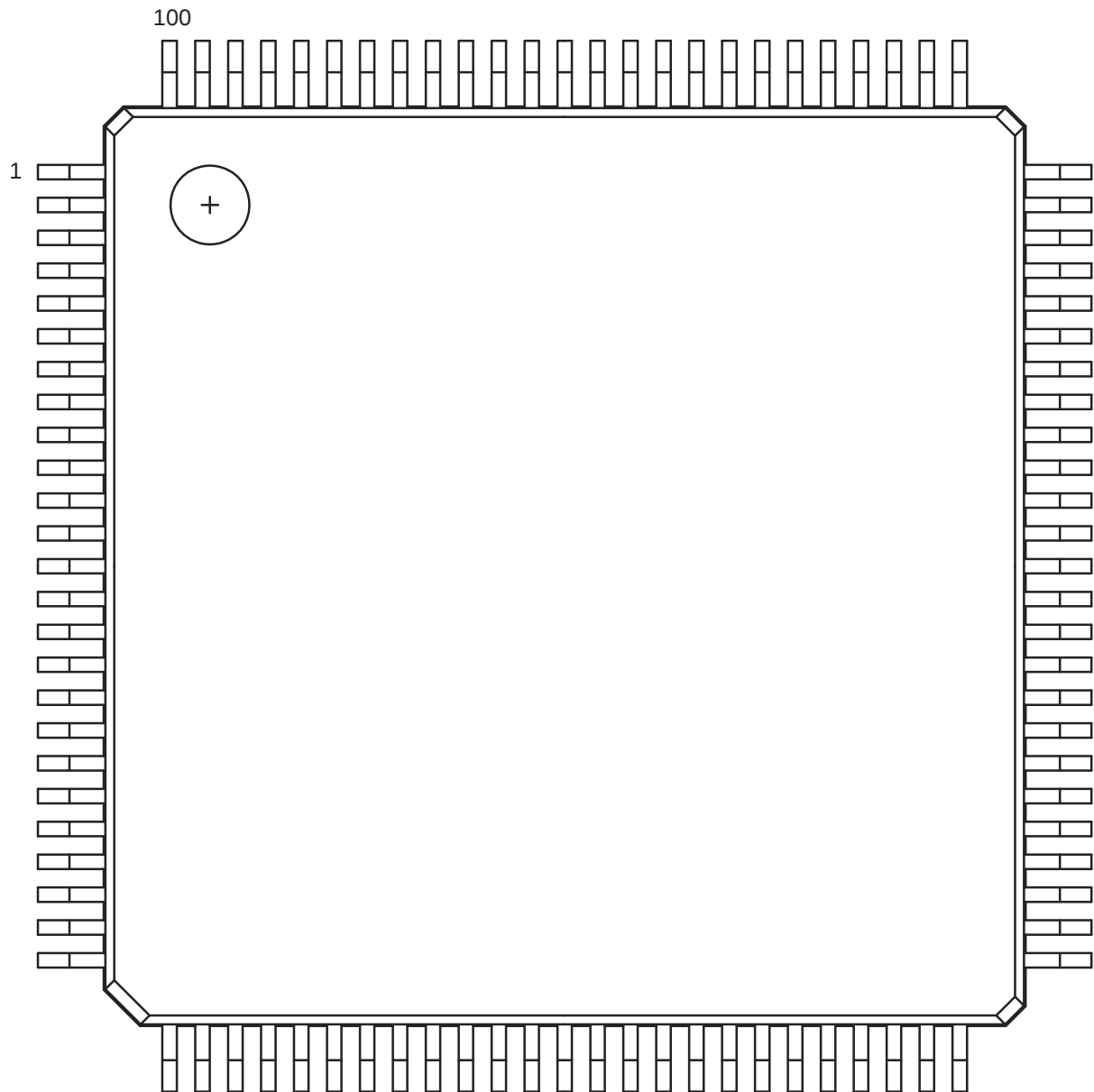


Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

VQ100



Note: This is the top view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

VQ100	
Pin Number	AGL250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO112PSB3
9	GND
10	GFB1/IO109PDB3
11	GFB0/IO109NDB3
12	VCOMPLF
13	GFA0/IO108NPB3
14	VCCPLF
15	GFA1/IO108PPB3
16	GFA2/IO107PSB3
17	VCC
18	VCCIB3
19	GFC2/IO105PSB3
20	GEC1/IO100PDB3
21	GEC0/IO100NDB3
22	GEA1/IO98PDB3
23	GEA0/IO98NDB3
24	VMV3
25	GNDQ
26	GEA2/IO97RSB2
27	FF/GE2/IO96RSB2
28	GEC2/IO95RSB2
29	IO93RSB2
30	IO92RSB2
31	IO91RSB2
32	IO90RSB2
33	IO88RSB2
34	IO86RSB2
35	IO85RSB2
36	IO84RSB2

VQ100	
Pin Number	AGL250 Function
37	VCC
38	GND
39	VCCIB2
40	IO77RSB2
41	IO74RSB2
42	IO71RSB2
43	GDC2/IO63RSB2
44	GDB2/IO62RSB2
45	GDA2/IO61RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO60USB1
58	GDC0/IO58VDB1
59	GDC1/IO58UDB1
60	IO52NDB1
61	GCB2/IO52PDB1
62	GCA1/IO50PDB1
63	GCA0/IO50NDB1
64	GCC0/IO48NDB1
65	GCC1/IO48PDB1
66	VCCIB1
67	GND
68	VCC
69	IO43NDB1
70	GBC2/IO43PDB1
71	GGB2/IO42PSB1
72	IO41NDB1

VQ100	
Pin Number	AGL250 Function
73	GBA2/IO41PDB1
74	VMV1
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GGB1/IO38RSB0
79	GGB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO29RSB0
83	IO27RSB0
84	IO25RSB0
85	IO23RSB0
86	IO21RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

FG144	
Pin Number	AGL1000 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO10RSB0
A6	GND
A7	IO44RSB0
A8	VCC
A9	IO69RSB0
A10	GBA0/IO76RSB0
A11	GBA1/IO77RSB0
A12	GNDQ
B1	GAB2/IO224PDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO13RSB0
B6	IO26RSB0
B7	IO35RSB0
B8	IO60RSB0
B9	GBB0/IO74RSB0
B10	GBB1/IO75RSB0
B11	GND
B12	VMV1
C1	IO224NDB3
C2	GFA2/IO206PPB3
C3	GAC2/IO223PDB3
C4	VCC
C5	IO16RSB0
C6	IO29RSB0
C7	IO32RSB0
C8	IO63RSB0
C9	IO66RSB0
C10	GBA2/IO78PDB1
C11	IO78NDB1
C12	GBC2/IO80PPB1

FG144	
Pin Number	AGL1000 Function
D1	IO213PDB3
D2	IO213NDB3
D3	IO223NDB3
D4	GAA2/IO225PPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO72RSB0
D8	GBC1/IO73RSB0
D9	GBB2/IO79PDB1
D10	IO79NDB1
D11	IO80NPB1
D12	GCB1/IO92PPB1
E1	VCC
E2	GFC0/IO209NDB3
E3	GFC1/IO209PDB3
E4	VCCIB3
E5	IO225NPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO91PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO93NDB1
E12	IO94NDB1
F1	GFB0/IO208NPB3
F2	VCOMPLF
F3	GFB1/IO208PPB3
F4	IO206NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO91NDB1
F9	GCB0/IO92NPB1
F10	GND
F11	GCA1/IO93PDB1
F12	GCA2/IO94PDB1

FG144	
Pin Number	AGL1000 Function
G1	GFA1/IO207PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO207NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO111PPB1
G9	IO96NDB1
G10	GCC2/IO96PDB1
G11	IO95NDB1
G12	GCB2/IO95PDB1
H1	VCC
H2	GFB2/IO205PDB3
H3	GFC2/IO204PSB3
H4	GEC1/IO190PDB3
H5	VCC
H6	IO105PDB1
H7	IO105NDB1
H8	GDB2/IO115RSB2
H9	GDC0/IO111NPB1
H10	VCCIB1
H11	IO101PSB1
H12	VCC
J1	GEB1/IO189PDB3
J2	IO205NDB3
J3	VCCIB3
J4	GEC0/IO190NDB3
J5	IO160RSB2
J6	IO157RSB2
J7	VCC
J8	TCK
J9	GDA2/IO114RSB2
J10	TDO
J11	GDA1/IO113PDB1
J12	GDB1/IO112PDB1

FG256	
Pin Number	AGL1000 Function
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL1000 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1

FG256	
Pin Number	AGL1000 Function
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2

FG484	
Pin Number	AGL1000 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO13RSB0
A7	IO18RSB0
A8	IO20RSB0
A9	IO26RSB0
A10	IO32RSB0
A11	IO40RSB0
A12	IO41RSB0
A13	IO53RSB0
A14	IO59RSB0
A15	IO64RSB0
A16	IO65RSB0
A17	IO67RSB0
A18	IO69RSB0
A19	NC
A20	VCCIB0
A21	GND
A22	GND
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	IO181RSB2
AA5	IO178RSB2
AA6	IO175RSB2
AA7	IO169RSB2
AA8	IO166RSB2
AA9	IO160RSB2
AA10	IO152RSB2
AA11	IO146RSB2
AA12	IO139RSB2
AA13	IO133RSB2
AA14	NC

Revision	Changes	Page
Revision 19	The following figures were deleted (SAR 29991). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 21770). Figure 2-36 • Write Access after Write onto Same Address Figure 2-37 • Read Access after Write onto Same Address Figure 2-38 • Write Access after Read onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-40 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	N/A 2-119 to 2-130
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 27395).	4-1
	The "CS81" pin table for AGL250 is new (SAR 22737).	4-5
	The CS121 pin table for AGL125 is new (SAR 22737).	
	The P3 function was revised in the "CS196" pin table for AGL250 (SAR 24800).	4-12
	The "QN132" pin table for AGL250 was added. The "FG144" pin table for AGL060 was added (SAR 33689)	4-35, 4-42
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "IGLOO Device Status" table indicates the status for each device in the device family.	N/A